# **Dual N-Channel 65 V (D-S) Super Junction MOSFET**

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}$ (m $\Omega$ )(TYP.)	I <sub>D</sub> (A) <sup>a, e</sup>	Q <sub>g</sub> (Typ.)			
65	13 at V <sub>GS</sub> = 10 V	40	9.5 nC			
	19 at V <sub>GS</sub> = 4.5 V	40				

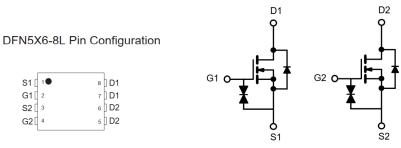
#### **FEATURES**

- DT-SJ Power MOSFET
- 100 %  $R_g$  and UIS Tested
- **ESD Protected**

# COMPLIANT

#### **APPLICATIONS**

- Notebook PC Core
- VRM/POL



**Top View** 

N1-Channel MOSFET

N2-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	65	\/	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Prais Current /T = 150 °C)	T <sub>C</sub> = 25 °C	1	40 <sup>a, d</sup>		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 100 °C	l I <sub>D</sub>	25.5 <sup>d</sup>		
Pulsed Drain Current		I <sub>DM</sub>	160	A	
Avalanche Current Pulse	L = 0.1 mH	I <sub>AS</sub>	26	7	
Single Pulse Avalanche Energy	L = 0.111111	E <sub>AS</sub>	31	mJ	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	40 <sup>a, d</sup>	А	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	D	51	10/	
Maximum Fower Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	32.6	W	
Operating Junction and Storage Temperature Range	је	T <sub>J</sub> , T <sub>stg</sub>	- 55 to150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, c</sup>	t ≤ 10 s	R <sub>thJA</sub>		62	°C/W	
Maximum Junction-to-Case	Steady State	R <sub>thJC</sub>		2.45	C/VV	

#### Notes:

- a. Based on T<sub>C</sub> = 25 °C.
  b. Surface mounted on 1" x 1" FR4 board.
  c. Maximum under steady state conditions is 62 °C/W.
  d. Calculated based on maximum junction temperature.





Parameter	Symbol	Test Conditions	Min .	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V, } I_{D} = 250  \mu\text{A}$	65			V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.0	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 20	uA	
Zara Cata Valtaria Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	1		1		
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	10 µA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A		13	16	0	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8 A		20	25	mΩ	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 20 A		35		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			429			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		177		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			11			
Total Gate Charge	Qg			9.5			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{A}$		1.2		nC	
Gate-Drain Charge	Q <sub>gd</sub>			2		1	
Gate Resistance	Rg	f = 1 MHz		110		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			160			
Rise Time	t <sub>r</sub>	$V_{DS} = 30 \text{ V}, R_{L} = 0.555 \Omega$		250		1	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 20 \text{ A}, V_{GS} = 10 \text{ V}, R_g = 6 \Omega$		1250		ns	
Fall Time	t <sub>f</sub>			740		1	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			40		
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				160	Α	
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = 1 A		0.6	1	V	
Body Diode Reverse Recovery Time t <sub>rr</sub>		L = 10 A di/dt = 100 A/v.c T = 05 °C		31		ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 10 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 \text{ °C}$		18		nC	

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

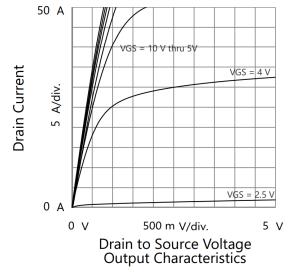
a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

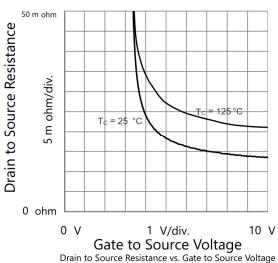
b. Guaranteed by design, not subject to production testing.

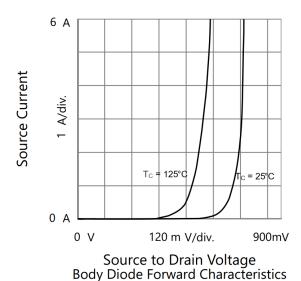
Din-Tek

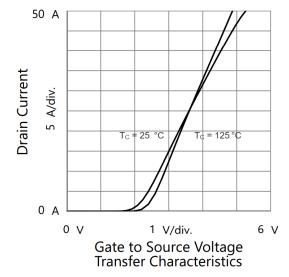
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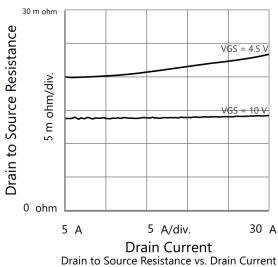
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

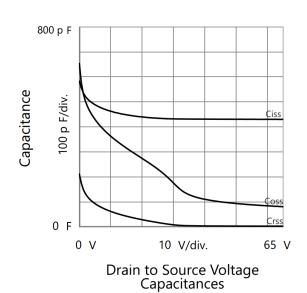




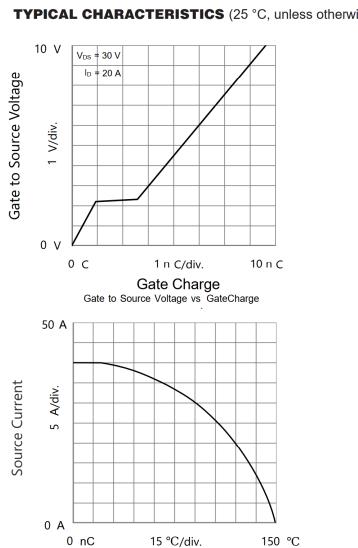






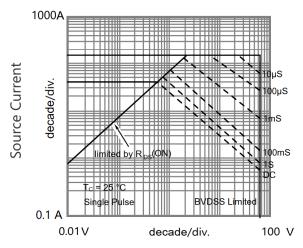


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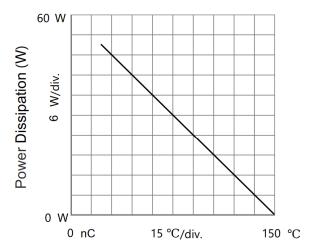


T<sub>C</sub> - Case Temperature

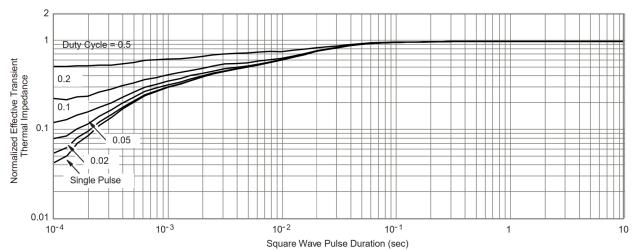
Current Derating



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient

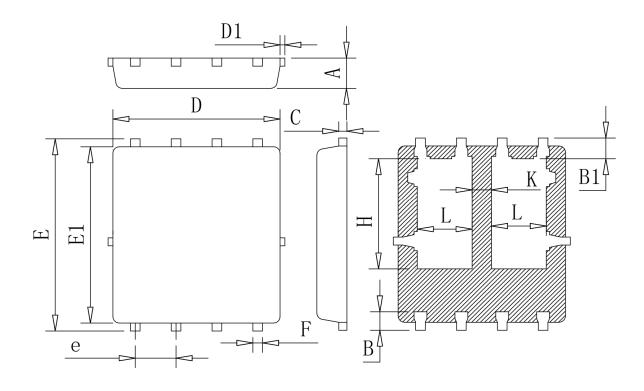


T<sub>C</sub> - Case Temperature
Power Derating



Normalized Thermal Transient Impedance, Junction-to-Case

## **DFN5X6-8L-D PACKAGE OUTLINE**



# COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	0.85	0.95	1.05
В	0.46	0.58	0.73
B1	0.52	0.65	0.78
С	0.18	0.254	0.32
D	4.70	5.20	5.50
D1	-	-	0.18
Е	5.75	6.05	6.35
E1	5.35	5.65	5.85
e	1.15	1.27	1.50
F	0.15	0.30	0.50
Н	3.15	3.47	3.80
L	1.35	1.70	2.10
K	0.35	0.60	1.00





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